



STT3PF20V

P-CHANNEL 20V - 0.14 Ω - 2.2A SOT23-6L
2.7-DRIVE STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STT3PF20V	20 V	< 0.20 Ω (@4.5V) < 0.25 Ω (@2.7V)	2.2 A

- TYPICAL R_{DS(on)} = 0.14 Ω (@4.5V)
- TYPICAL R_{DS(on)} = 0.20 Ω (@2.7V)
- ULTRA LOW THRESHOLD GATE DRIVE (2.7V)
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY

DESCRIPTION

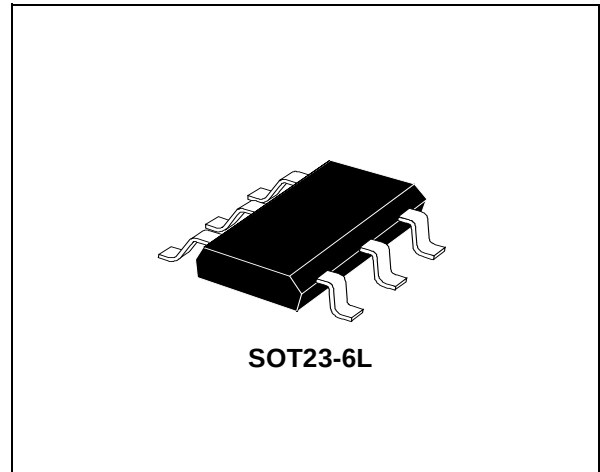
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

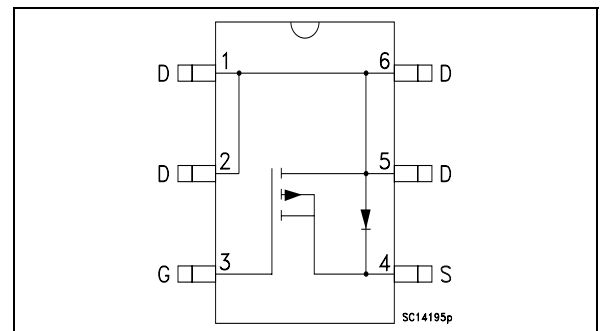
- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT
- CELLULAR

MARKING

- STP2



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	20	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	20	V
V _{GS}	Gate- source Voltage	± 12	V
I _D	Drain Current (continuous) at T _C = 25°C	2.2	A
I _D	Drain Current (continuous) at T _C = 100°C	1.39	A
I _{DM} (●)	Drain Current (pulsed)	8.8	A
P _{tot}	Total Dissipation at T _C = 25°C	1.6	W

(●) Pulse width limited by safe operating area.

Note: P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

STT3PF20V

THERMAL DATA

Rthj-amb T_j T_{stg}	(*) Thermal Resistance Junction-ambient Max. Operating Junction Temperature Storage Temperature	Max	78 -55 to 150 -55 to 150	°C/W °C °C
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(*) Mounted on a 1 inch pad of 2 oz. Cu in FR-4 board

(**) Mounted on a minimum pad of 2 oz. Cu in FR-4 board

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	20			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 12\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\text{ }\mu\text{A}$	0.6			V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 4.5\text{ V}$ $I_D = 1\text{ A}$ $V_{GS} = 2.7\text{ V}$ $I_D = 1\text{ A}$		0.14 0.20	0.20 0.25	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} = 15\text{ V}$ $I_D = 1\text{ A}$		4		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 15\text{ V}$ $f = 1\text{ MHz}$, $V_{GS} = 0$		315 87 17		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 10\text{ V}$ $I_D = 1\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		38 30		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 10\text{ V}$ $I_D = 2\text{ A}$ $V_{GS} = 4.5\text{ V}$		3.5 0.34 0.8	4.7	nC nC nC

SWITCHING OFF

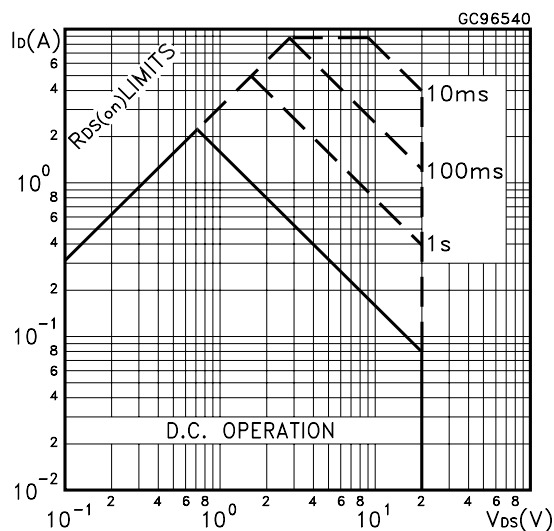
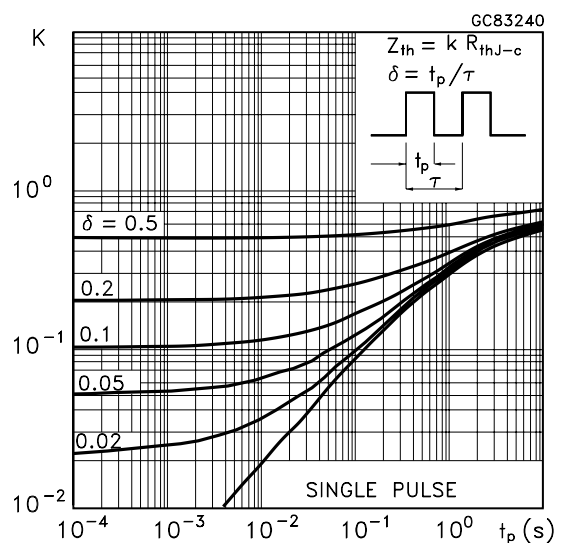
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 10\text{ V}$ $I_D = 1\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		45 11		ns ns

SOURCE DRAIN DIODE

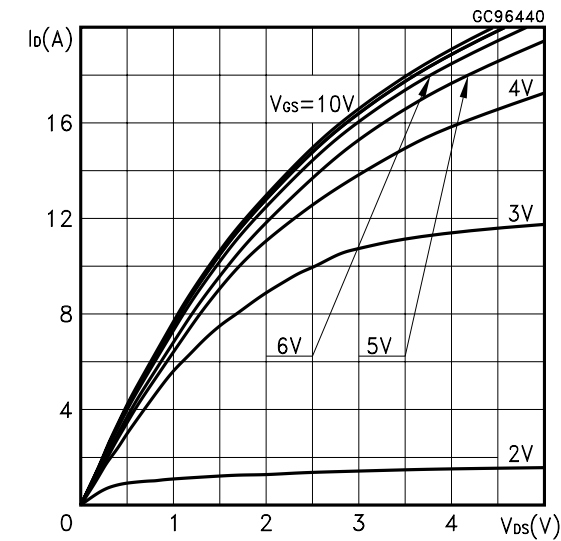
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				2.2 8.8	A A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 2\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 2\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 10\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		15 7.5 1		ns nC A

($\ast$) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

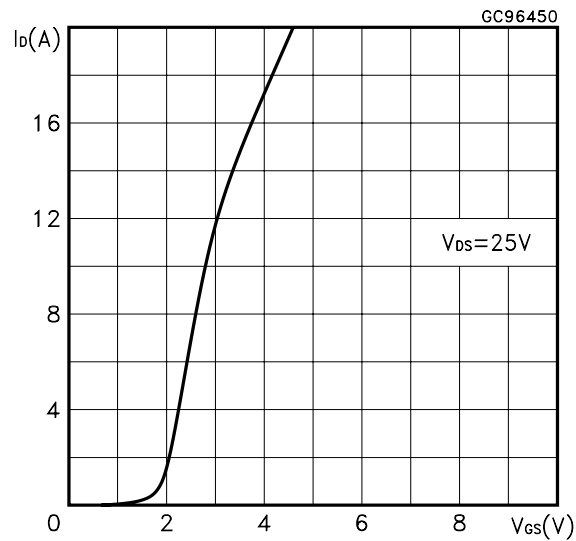
($\bullet$) Pulse width limited by safe operating area.

Safe Operating Area**Thermal Impedance**

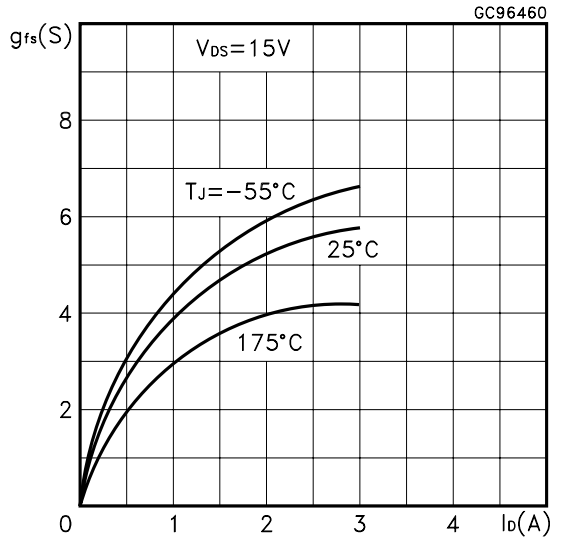
Output Characteristics



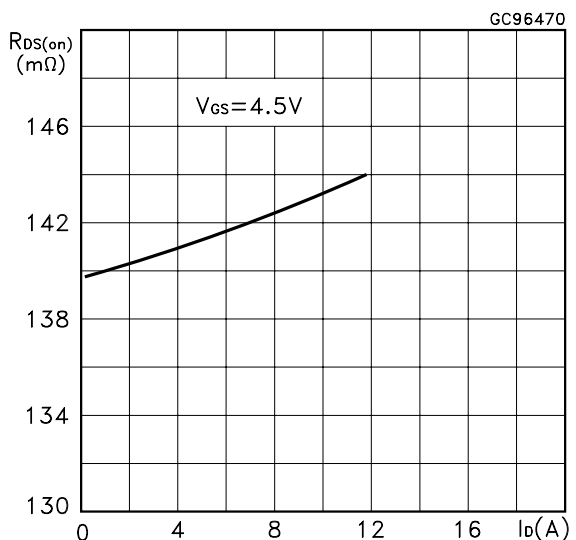
Transfer Characteristics



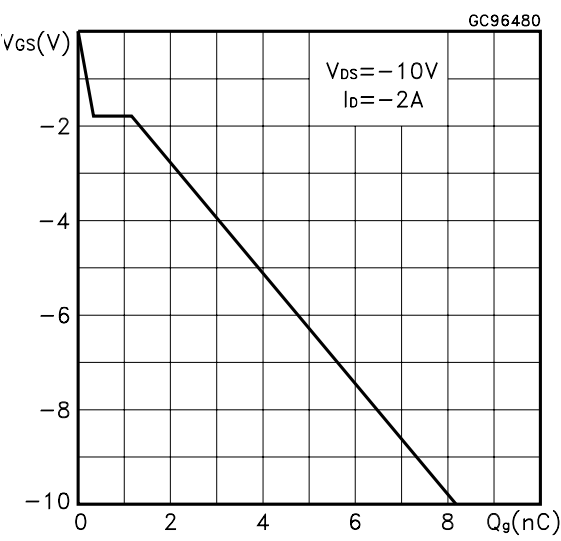
Transconductance



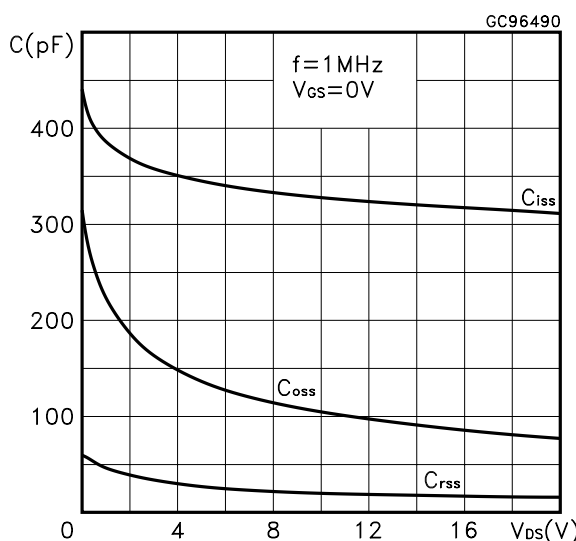
Static Drain-source On Resistance



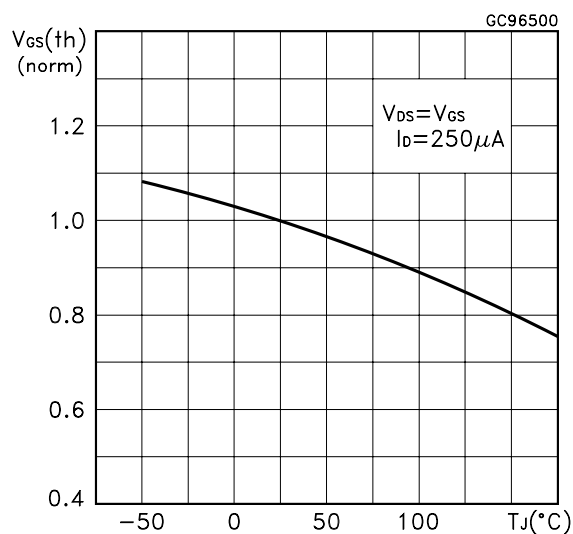
Gate Charge vs Gate-source Voltage



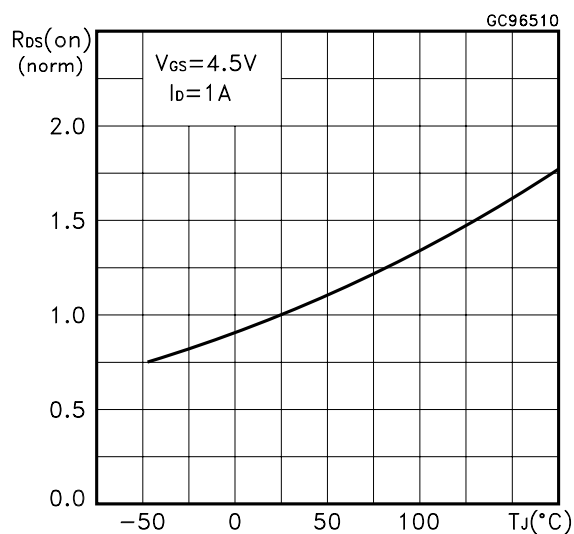
Capacitance Variations



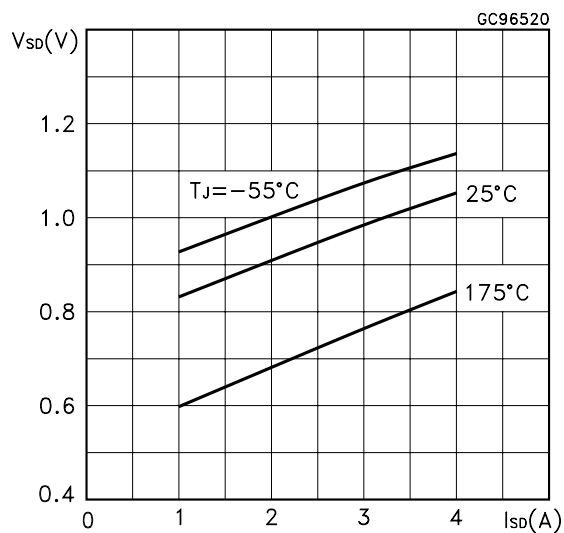
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

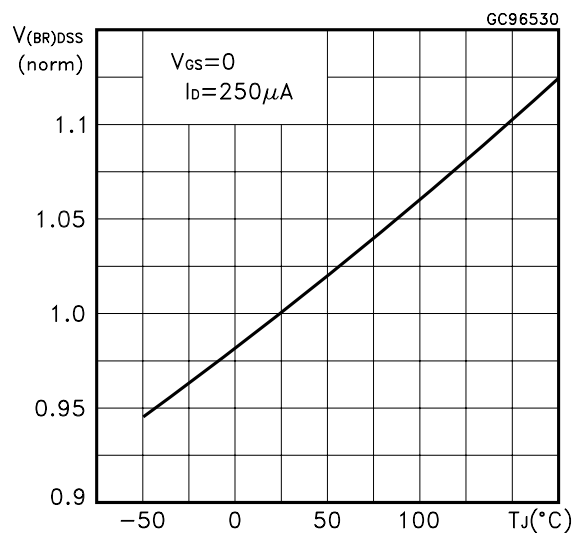


Fig. 1: Unclamped Inductive Load Test Circuit

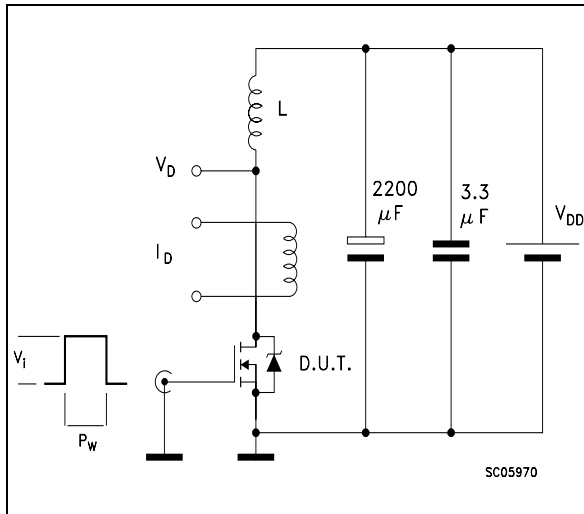


Fig. 2: Unclamped Inductive Waveform

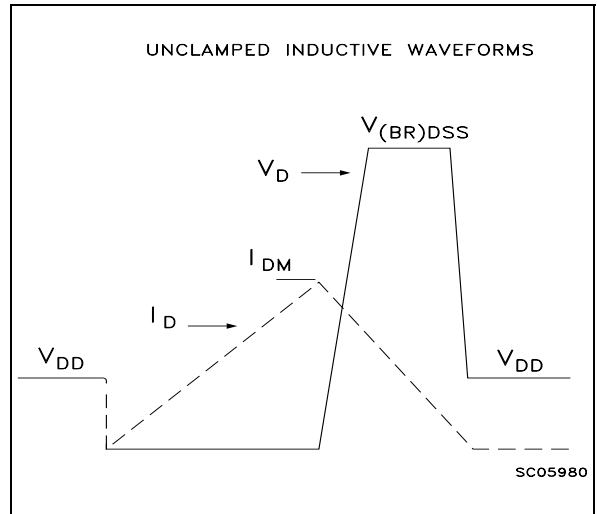


Fig. 3: Switching Times Test Circuits For Resistive Load

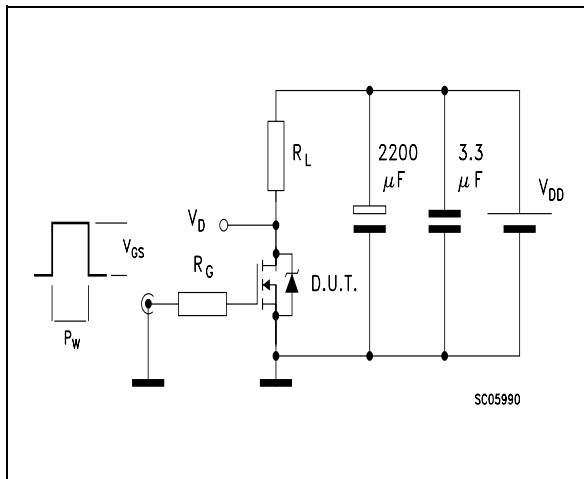


Fig. 4: Gate Charge test Circuit

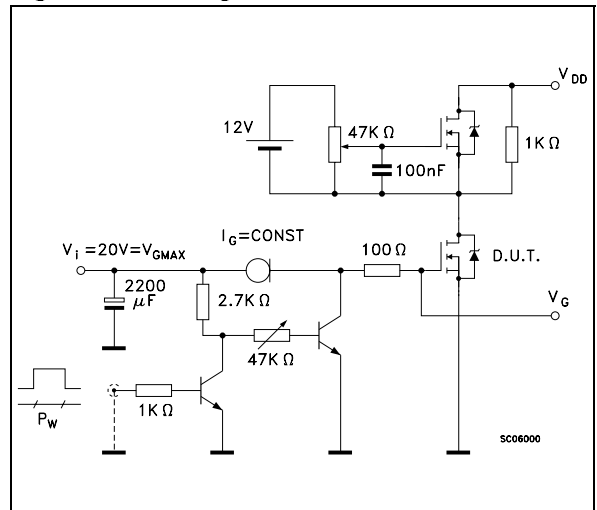
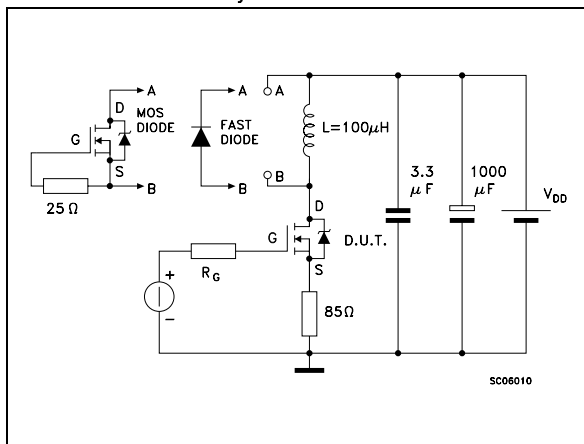
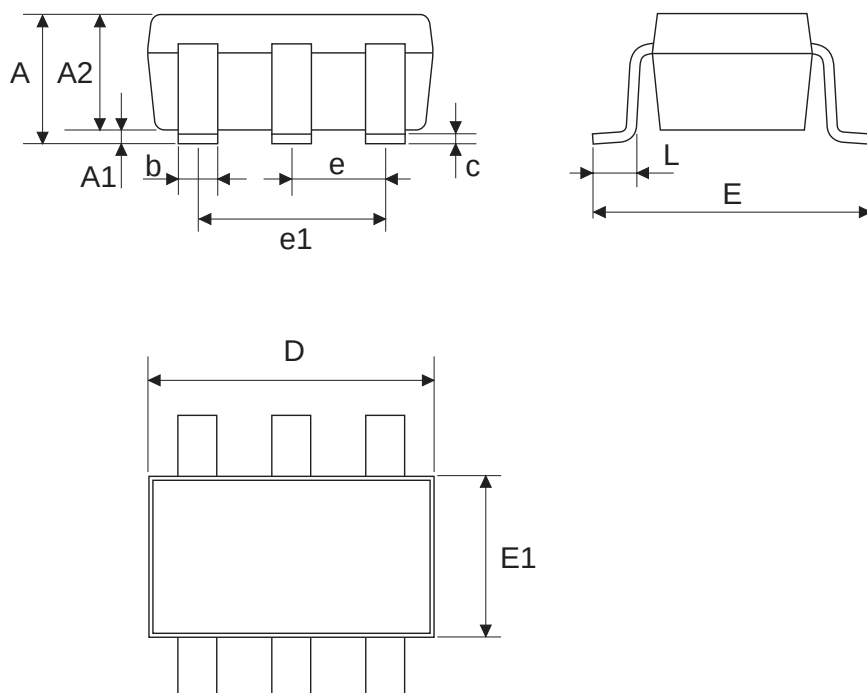


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SOT23-6L MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	0.035		0.057
A1	0.00		0.15	0.000		0.006
A2	0.90		1.30	0.035		0.051
b	0.25		0.50	0.010		0.020
C	0.09		0.20	0.004		0.008
D	2.80		3.10	0.110		0.122
E	2.60		3.00	0.102		0.118
E1	1.50		1.75	0.059		0.069
L	0.35		0.55	0.014		0.022
e		0.95			0.037	
e1		1.90			0.075	



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